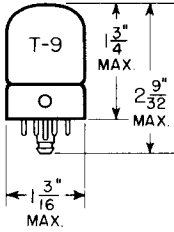


TUNG-SOL

PENTODE



GLASS BULB

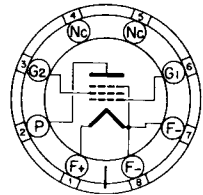
COATED FILAMENT

FILAMENT

1.2 VOLTS 130 MA.

DC

ANY MOUNTING POSITION



BOTTOM VIEW

LOCK-IN
8 PIN BASE
58F

THE 1AB5 IS A FILAMENTARY TYPE PENTODE VOLTAGE AMPLIFIER USING THE LOCK-IN CONSTRUCTION. IT IS DESIGNED FOR USE AS A MIXER OR RF AMPLIFIER IN CIRCUITS REQUIRING A TUBE WITH HIGHER TRANSCONDUCTANCE THAN THE 1LN5.

DIRECT INTERELECTRODE CAPACITANCES

WITH RMA SHIELD #308 CONNECTED TO NEGATIVE FILAMENT

GRID TO PLATE: (G ₁ TO P) MAX.	0.25	μf
INPUT: G ₁ TO (F+G ₂ +G ₃)	2.8	μf
OUTPUT: P TO (F+G ₂ +G ₃)	4.2	μf

RATINGS

INTERPRETED ACCORDING TO RMA STANDARD M8-210

FILAMENT VOLTAGE	1.2	VOLTS
FILAMENT CURRENT	130	MA.
MAXIMUM PLATE VOLTAGE	150	VOLTS
MAXIMUM GRID #2 VOLTAGE	150	VOLTS
MAXIMUM POSITIVE DC GRID #1 VOLTAGE	0	VOLTS
MAXIMUM PLATE DISSIPATION	1	WATT
MAXIMUM GRID #2 DISSIPATION	0.3	WATT

TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

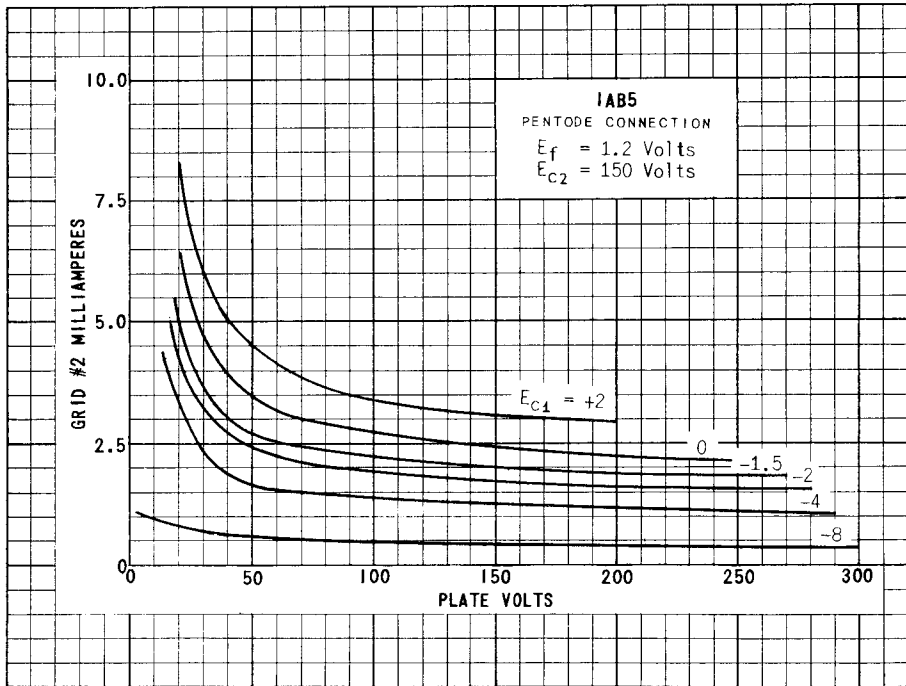
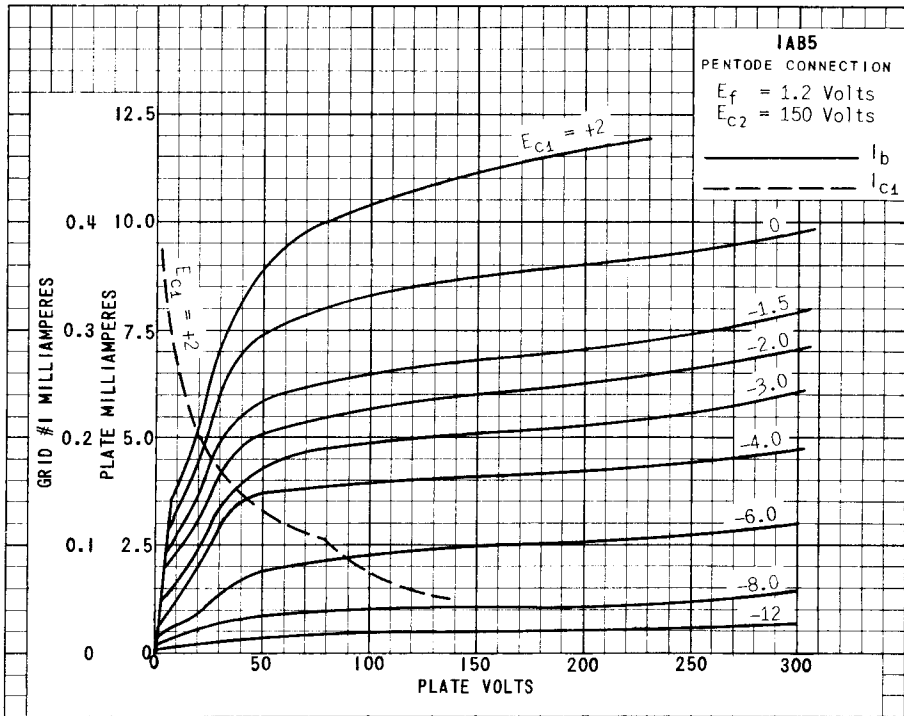
CLASS A₁ AMPLIFIER

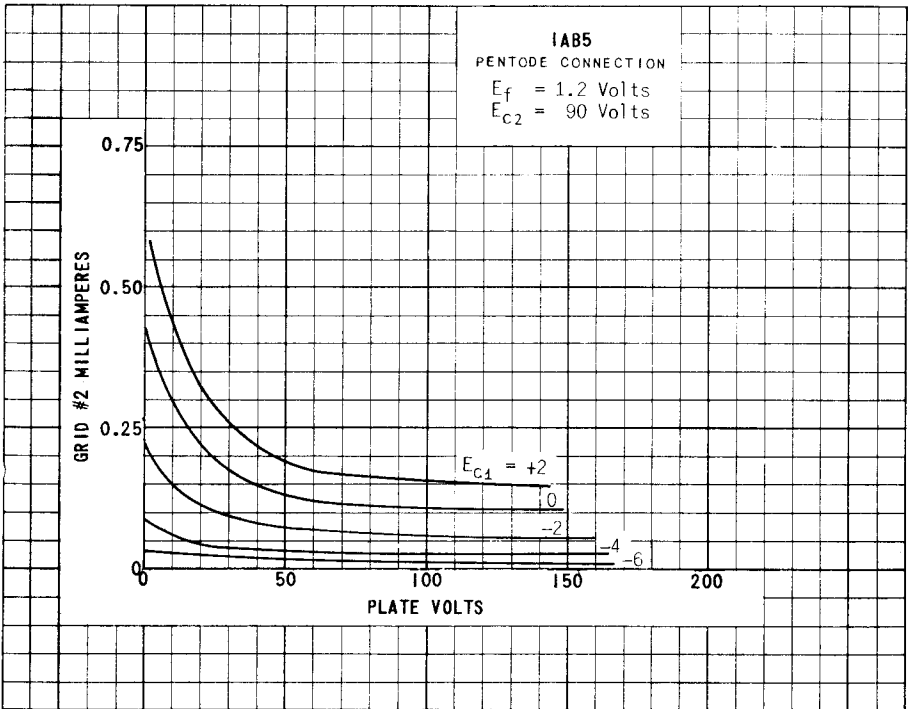
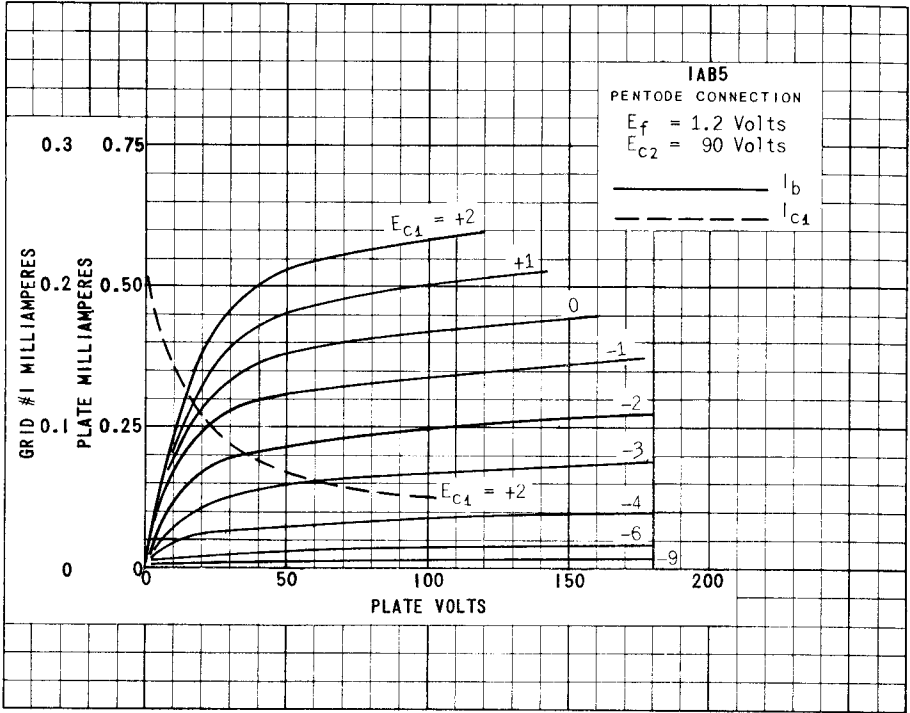
FILAMENT VOLTAGE	1.2	1.2	VOLTS
FILAMENT CURRENT	130	130	MA.
PLATE VOLTAGE	90	150	VOLTS
GRID #2 VOLTAGE	90	150	VOLTS
GRID #1 VOLTAGE	0 ^A	-1.5	VOLTS
GRID #1 RESISTOR (SELF BIAS)	---	170	OHMS
PLATE RESISTANCE (APPROX.)	0.275	0.125	ME GOHM
TRANSCONDUCTANCE	1 100	1 350	μMHOS
PLATE CURRENT	3.5	6.8	MA.
GRID #2 CURRENT	0.8	2	MA.
GRID #1 VOLTAGE (APPROX.) FOR G _m = 10 μMHOS	-14	-23	VOLTS
GRID #1 VOLTAGE (APPROX.) FOR G _m = 725 μMHOS	-3	-6	VOLTS

^A GRID #1 RESISTOR SHOULD BE 1 MEGOHM UNDER CONDITIONS OF ZERO-BIAS.

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IAB5

